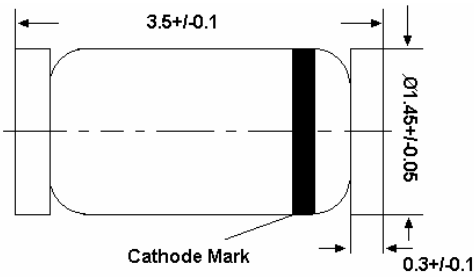


SILICON EPITAXIAL PLANAR DIODE

Features

- Small package
- Low forward voltage
- Fast reverse recovery time
- Small total capacitance



Glass case MiniMELF
Dimensions in mm

Applications

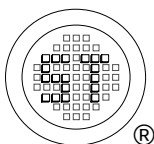
Extreme fast switches

Absolute Maximum Ratings (T_j = 25°C)

Parameter	Symbol	Value	Unit
Maximum Peak Reverse Voltage	V _{RM}	85	V
Reverse Voltage	V _R	80	V
Maximum Peak Forward Current	I _{FM}	200	mA
Surge Current (10ms)	I _{FSM}	1	A
Average Forward Current	I _o	100	mA
Power Dissipation	P _{tot}	200	mW
Junction Temperature	T _j	125	°C
Storage Temperature Range	T _s	-55 ... +125	°C

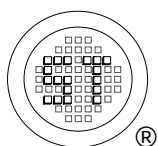
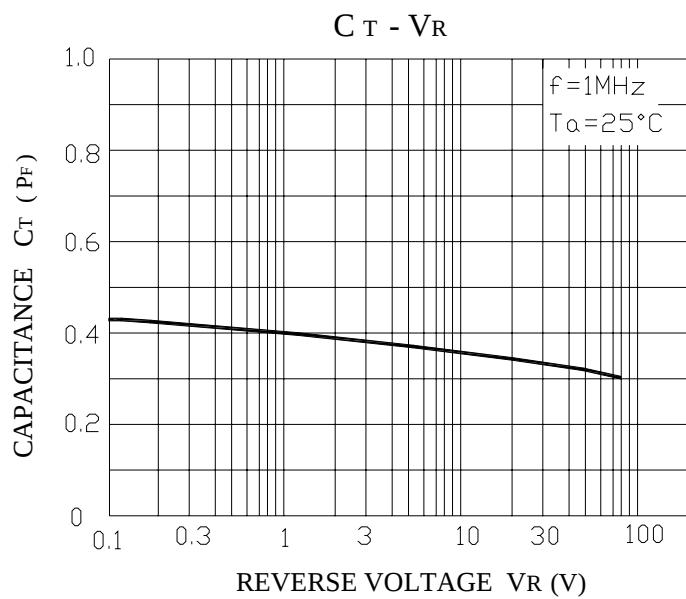
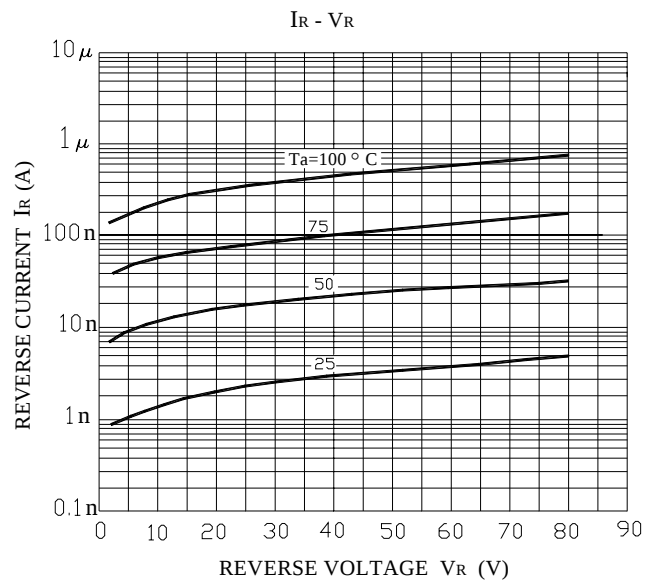
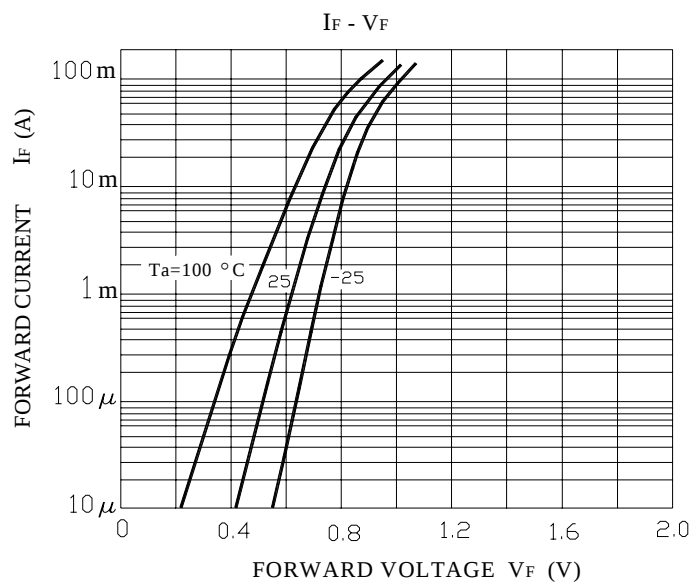
Characteristics at T_j = 25 °C

Parameter	Test Conditions	Symbol	Min	Typ	Max	Unit
Forward Voltage	I _F = 1mA	V _F	-	0.62	-	V
	I _F = 10mA	V _F	-	0.75	-	V
	I _F = 100mA	V _F	-	0.98	1.2	V
Reverse Current	V _R = 30V	I _R	-	-	0.1	μA
	V _R = 80V	I _R	-	-	0.5	μA
Total Capacitance	V _R = 0, f = 1MHz	C _T	-	0.5	3	pF
Reverse Recovery Time	I _F = 10mA	t _{rr}	-	1.6	4	ns

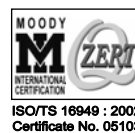


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Dated : 07/02/2003